

**Amendments to the Specification:**

On page 1, at line 5, insert the following paragraph:

This application claims benefit of priority to German Patent Application No. DE 10233208.8, filed July 22, 2002.

On page 2, at line 17, insert the following heading:

**BRIEF SUMMARY**

On page 4, before line 1, insert the following heading:

**BREIF DESCRIPTION OF THE DRAWING**

On page 5, before line 1, insert the following heading:

**DETAILED DESCRIPTION**

Please delete page 25.

Please replace the Abstract with the following amended Abstract:

**ABSTRACT**

**SEMICONDUCTOR COMPONENT WITH TRENCH  
ISOLATION AND ASSOCIATED FABRICATION METHOD**

The invention relates to a semiconductor component with trench isolation and to an associated fabrication method, a trench isolation (~~STI, TTI~~) having a deep isolation trench with a covering insulation layer (~~10, 11~~), a side wall insulation layer (~~6~~) and an electrically conductive filling layer (~~7~~), which is electrically connected to a predetermined doping region (~~4~~) of the semiconductor substrate in a bottom region of the trench. The use of a trench contact (~~DTG~~), which has a deep contact trench with a side wall insulation layer (~~6~~) and an electrically conductive filling layer (~~7~~), which is likewise electrically connected to the predetermined doping region (~~4~~) of the semiconductor substrate in a bottom region of the contact trench, makes it possible to improve the electrical shielding properties with a reduced area requirement.

~~Figure 3~~